Appl. No. 10/696,007 Reply to Office Action of December 3, 2004 Attorney Docket No. 2001.0808B/24061.374 Customer No. 42717

Amendments to the Specification

On page 1 of the specification, please replace the paragraph previously added by amendment before line 1 with the following amended paragraph:

This is a division of Patent Application social number U.S. Serial No. 10/146,287, filing date 5/15/02, A New filed May 15, 2002 and entitled "Process For Integration Of A High Dielectric Gestant Constant Gate Insulator Layer In A Gmos CMOS Device" (now U.S. Patent No. 6.656,764 issued December 2, 2003), assigned to the same assigned as the present invention.